

Title (en)
APPARATUS FOR HEATING SEMICONDUCTOR WAFERS

Publication
EP 0290692 B1 19930908 (EN)

Application
EP 87304297 A 19870514

Priority
EP 87304297 A 19870514

Abstract (en)
[origin: EP0290692A1] Radiation heating of a semiconductor wafer employs first and second pluralities (30; 32) of spaced and skewed elongate parallel lamps (1 to 10; 11 to 20). Lamps in each plurality are grouped beginning with the innermost lamps and extending to the outermost lamps. Each group of lamps in one plurality of lamps are interconnected with a group of lamps in the other plurality of lamps whereby the interconnected groups of lamps are simultaneously and equally energized. Lamp voltage is modulated in accordance with a preestablished table for each size of wafer and temperature cycle. Alternatively, temperature sensors (38) can be employed to provide feedback to a computer controlled modulator. The lamps in the different groups can be selected to have different steady state power intensities for a given voltage thereby to establish a desired temperature gradient.

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IPC 8 full level
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CPC (source: EP)
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